

2.1. INTRODUCTION TO BASIC CRYSTALLOGRAPHY

crystal. The term $1/V^2$ can be explained as follows. In a mosaic block, all unit cells scatter in phase. For a given volume of the individual blocks, the number of unit cells in a mosaic block, as well as the scattering amplitude, is proportional to $1/V$. The scattered intensity is then proportional to $1/V^2$. Because of the finite reflection width, scattering occurs not only for the reciprocal-lattice point when it is on the Ewald sphere, but also for a small volume around it. Since the sphere has radius $1/\lambda$, the solid angle for scattering, and thus the intensity, is proportional to $1/(1/\lambda)^2 = \lambda^2$.

However, in equation (2.1.6.1), the scattered intensity is proportional to λ^3 . The extra λ dependence is related to the time t it takes for the reciprocal-lattice 'point' to pass through the surface of the Ewald sphere. With an angular speed of rotation ω , a reciprocal-lattice point at a distance $1/d$ from the origin of the reciprocal lattice moves with a linear speed $v = (1/d)\omega$ if the rotation axis is normal to the plane containing the incident and reflected beam. For the actual passage through the surface of the Ewald sphere, the component perpendicular to the surface is needed: $v_{\perp} = (1/d)\omega \cos \theta = \omega \sin 2\theta/\lambda$. Therefore, the time t required to pass through the surface is proportional to $(1/\omega)(\lambda/\sin 2\theta)$. This introduces the extra λ term in equation (2.1.6.1) as well as the ω dependence and a $1/\sin 2\theta$ term. The latter represents the Lorentz factor L . It is a geometric correction factor for the hkl reflections; here it is $1/\sin 2\theta$, but it is different for other data-collection geometries.

The factor P in equation (2.1.6.1) is the polarization factor. For the polarized incident beam used in deriving equation (2.1.4.1a), $P = \sin^2 \varphi$, where φ is the angle between the polarization direction of the beam and the scattering direction. It is easy to verify that $\varphi = 90^\circ - 2\theta$, where θ is the reflecting angle (Fig. 2.1.4.9). P depends on the degree of polarization of the incident beam. For a completely unpolarized beam, $P = (1 + \cos^2 2\theta)/2$.

In equation (2.1.6.1), T is the transmission factor: $T = 1 - A$, where A is the absorption factor. When X-rays travel through matter, they suffer absorption. The overall absorption follows Beer's law:

$$I = I_0 \exp(-\mu d),$$

where I_0 is the intensity of the incident beam, d is the path length in the material and μ is the total linear absorption coefficient. μ can be obtained as the sum of the atomic mass absorption coefficients of the elements $(\mu_m)_i$:

$$\mu = \rho \sum_i g_i (\mu_m)_i,$$

where ρ is the density of the absorbing material and g_i is the mass fraction of element i .

Atomic mass absorption coefficients $(\mu_m)_i$ for the elements are listed in Tables 4.2.4.3 (and 4.2.4.1) of *ITC* (1999) as a function of a large number of wavelengths. The absorption is wavelength-dependent and is generally much stronger for longer wavelengths. This is the result of several processes. For the X-ray wavelengths applied in crystallography, the processes are scattering and photoelectric absorption. Moreover, at the reflection position, the intensity may be reduced by extinction.

Scattering is the result of a collision between the X-ray photons and the electrons. One can distinguish two kinds of scattering: Compton scattering and Rayleigh scattering. In Compton scattering, the photons lose part of their energy in the collision process (inelastic scattering), resulting in scattered photons with a lower energy and a longer wavelength. Compton scattering contributes to the background in an X-ray diffraction experiment. In Rayleigh scattering, the photons are elastically scattered, do not lose energy, and leave the material with their wavelength unchanged. In a crystal, they interfere with each other and give rise to the Bragg

reflections. Between the Bragg reflections, there is no loss of energy due to elastic scattering and the incident beam is hardly reduced. In the Bragg positions, if the reduction in intensity of the incident beam due to elastic scattering can still be neglected, the crystal is considered an ideal mosaic. For non-ideal mosaic crystals, the beam intensity is reduced by *extinction*:

(1) The blocks are too large, and multiple reflection occurs within a block. At each reflection process, the phase angle shifts $\pi/2$ (Section 2.1.4.3.2). After two reflections, the beam travels in the same direction as the incident beam but with a phase difference of π , and this reduces the intensity.

(2) The angular spread of the blocks is too small. The incident beam is partly reflected by blocks close to the surface and the resulting beam is the incident beam for the lower-lying blocks that are also in reflecting position.

Extinction is not a serious problem in protein X-ray crystallography.

Absorption curves as a function of the X-ray wavelength show anomalies at absorption edges. At such an edge, electrons are ejected from the atom or are elevated to a higher-energy bound state, the photons disappear completely and the X-ray beam is strongly absorbed. This is called *photoelectric absorption*. At an absorption edge, the frequency of the X-ray beam ν is equal to the frequency ν_K, ν_L or ν_M corresponding to the energy of the K, L , or M state. According to equation (2.1.4.4), anomalous scattering is maximal at an absorption edge.

2.1.7. Calculation of electron density

In equation (2.1.4.6), the wave $W_{\text{cr}}(\mathbf{S})$ scattered by the crystal is given as the sum of the atomic contributions, as in equation (2.1.4.5) for the scattering by a unit cell. In the derivation of equation (2.1.4.5), it is assumed that the atoms are spherically symmetric (Section 2.1.4.3) and that density changes due to chemical bonding are neglected. A more exact expression for the wave scattered by a crystal, in the absence of anomalous scattering, is

$$W_{\text{cr}}(\mathbf{S}) = \int_{\text{crystal}} \rho(\mathbf{r}) \exp(2\pi i \mathbf{r} \cdot \mathbf{S}) \, dV_{\text{real}}. \quad (2.1.7.1)$$

The integration is over all electrons in the crystal. $\rho(\mathbf{r})$ is the electron-density distribution in each unit cell. The operation on the electron-density distribution in equation (2.1.7.1) is called Fourier transformation, and $W_{\text{cr}}(\mathbf{S})$ is the Fourier transform of $\rho(\mathbf{r})$. It can be shown that $\rho(\mathbf{r})$ is obtained by an inverse Fourier transformation:

$$\rho(\mathbf{r}) = \int_{\mathbf{S}} W_{\text{cr}}(\mathbf{S}) \exp(-2\pi i \mathbf{r} \cdot \mathbf{S}) \, dV_{\text{reciprocal}}. \quad (2.1.7.2)$$

In contrast to $\rho(\mathbf{r})$, $W_{\text{cr}}(\mathbf{S})$ is not a continuous function but, because of the Laue conditions, it is only different from zero at the reciprocal-lattice points \mathbf{h} ($= hkl$). In equation (2.1.4.6), $W_{\text{cr}}(\mathbf{S})$ is the product of the structure factor and three delta functions. The structure factor at the reciprocal-lattice points is $F(\mathbf{h})$, and the product of the three delta functions is $1/V$, the volume of one reciprocal unit cell. Therefore, $W_{\text{cr}}(\mathbf{S})$ in equation (2.1.7.2) can be replaced by $F(\mathbf{h})/V$, and equation (2.1.7.2) itself by

$$\rho(\mathbf{r}) = (1/V) \sum_{\mathbf{h}} F(\mathbf{h}) \exp(-2\pi i \mathbf{r} \cdot \mathbf{h}). \quad (2.1.7.3)$$

If x, y and z are fractional coordinates in the unit cell, $\mathbf{r} \cdot \mathbf{S} = (\mathbf{a} \cdot x + \mathbf{b} \cdot y + \mathbf{c} \cdot z) \cdot \mathbf{S} = \mathbf{a} \cdot \mathbf{S} \cdot x + \mathbf{b} \cdot \mathbf{S} \cdot y + \mathbf{c} \cdot \mathbf{S} \cdot z = hx + ky + lz$, and an alternative expression for the electron density is

$$\rho(xyz) = (1/V) \sum_{\mathbf{h}} \sum_{\mathbf{k}} \sum_{\mathbf{l}} F(hkl) \exp[-2\pi i(hx + ky + lz)]. \quad (2.1.7.4)$$

Instead of expressing $F(\mathbf{S})$ as a summation over the atoms [equation (2.1.4.5)], it can be expressed as an integration over the